TOSHIBA

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK1062

High Speed Switching Applications Analog Switching Applications Interface Applications

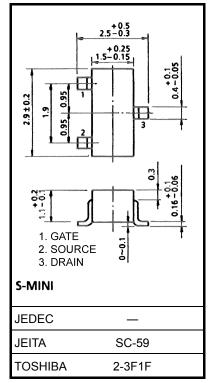
- Excellent switching time: ton = 14 ns (typ.)
- High forward transfer admittance: $|Y_{fs}| = 100 \text{ ms} (\text{min})$

@I_D = 50 mA

- Low on resistance: $RDS(ON) = 0.6 \Omega$ (typ.) @ ID = 50 mA
- Enhancement-mode
- Complementary to 2SJ168

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC	I _D	200	mA	
	Pulse	I _{DP}	800		
Drain power dissipation (Ta = 25° C)		PD	200	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

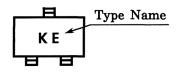


Weight: 0.012 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking



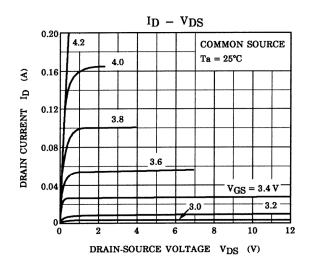
Unit: mm

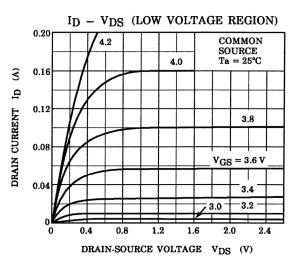
Electrical Characteristics (Ta = 25°C)

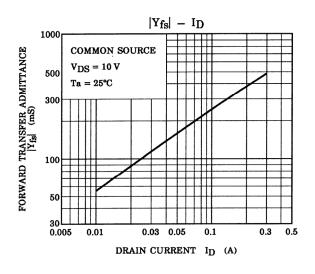
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS}=\pm 10~V,~V_{DS}=0$	_	_	±100	nA
Drain cut-off current		I _{DSS}	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0$			10	μA
Drain-source brea	akdown voltage	V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	60			V
Gate threshold vo	oltage	V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2		3.5	V
Forward transfer	admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 50 \text{ mA}$	100			mS
Drain-source ON	resistance	R _{DS (ON)}	$I_D = 50$ mA, $V_{GS} = 10$ V	_	0.6	1.0	Ω
Drain-source ON voltage		V _{DS (ON)}	$I_D = 50$ mA, $V_{GS} = 10$ V	_	30	50	mV
Input capacitance	9	C _{iss}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$	_	55	65	pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$	_	13	18	pF
Output capacitance		C _{oss}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$	_	40	50	pF
Switching time	Rise time	tr	$I_{D} = 100 \text{ mA}$ $I_{D} = 100 \text{ mA}$ $I_{D} = 100 \text{ mA}$ V_{N} $V_{D} = 10 \mu \text{S}$ $V_{DD} = 30 \text{ V}$	—	8	_	ns
	Turn-on time	t _{on}		_	14	_	
	Fall time	t _f			35	_	
	Turn-off Time	t _{off}	V_{IN} : t_r , $t_f < 5 \text{ ns}$ D.U \leq 1% (Z _{out} = 50 Ω)		75		

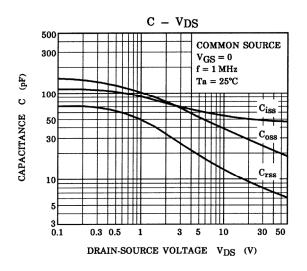
Note: This transistor is the electrostatic sensitive device. Please handle with caution.

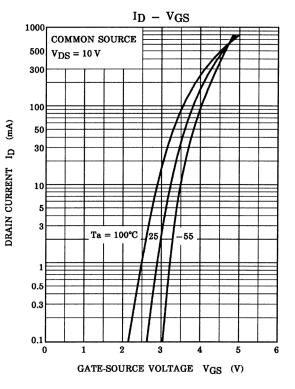
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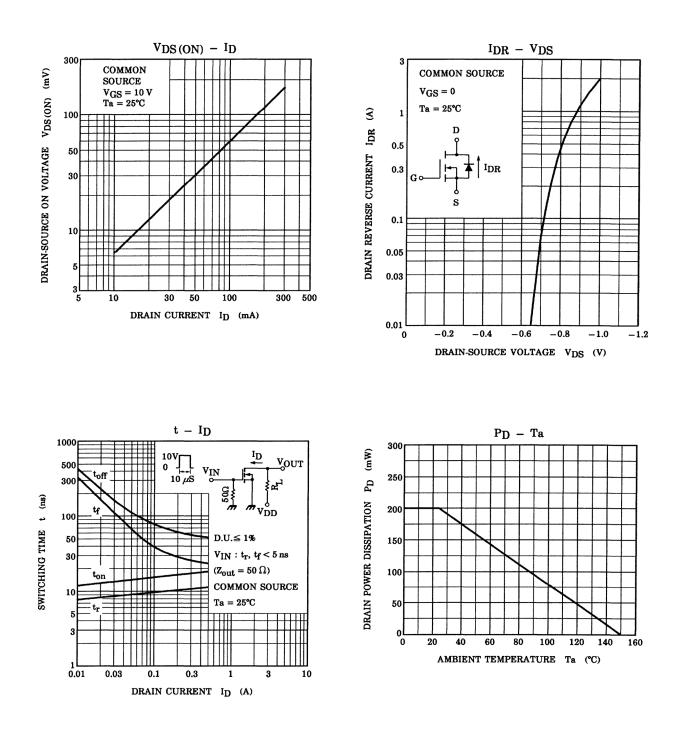








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20070701-EN GENERAL

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